Side-by-side Comparison of the Independent Claims of the '678 patent

Claim 1	Claim 11	Claim 13
1. A method of fabricating a microelectronic device, comprising the steps of:	11. A method of fabricating a microelectronic device, comprising the steps of:	13. A method of fabric microelectronic device the steps of:
furnishing a first substrate having an etchable layer, an etch-stop layer overlying the etchable layer, and a wafer overlying the etch-stop layer;	furnishing a first substrate having an etchable layer, an etch-stop layer overlying the etchable layer, and a wafer overlying the etch-stop layer;	furnishing a first subst silicon etchable layer, dioxide etch-stop laye the silicon layer, and a silicon wafer overlying stop layer, the wafer h surface not contacting dioxide layer;
forming a microelectronic circuit element in the exposed side of the wafer of the first substrate opposite to the side overlying the etch-stop layer;	forming a microelectronic circuit element in the exposed side of the wafer of the first substrate opposite the side overlying the etch-stop layer;	forming a microelectr element in the front su single-crystal silicon w
attaching the wafer of the first substrate to a second substrate; and	attaching the wafer of the first substrate to a second substrate, the second substrate having a second microelectronic circuit element therein;	attaching the front su single-crystal silicon w side of a second substr
	making an electrical contact from the microelectronic circuit element	

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	in the wafer of the first substrate to the second microelectronic circuit element on the second substrate; and	
etching away the etchable layer of the first substrate down to the etch-stop layer.	etching away the etchable layer of the first substrate down to the etch-stop layer; and	etching away the s layer down to the etch-stop layer
		using an etchant t silicon layer but no dioxide layer.
	forming an electrical connection to the microelectronic circuit element in the wafer of the first substrate through the etch-stop layer.	

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